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ON Semiconductor T2322B

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Distributor of ON Semiconductor: Excellent Integrated System Limited Datasheet of T2322B - TRIAC SENS GATE 200V TO225AA Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

# T2322B

# **Sensitive Gate Triacs**

# **Silicon Bidirectional Thyristors**

Designed primarily for ac power switching. The gate sensitivity of these triacs permits the use of economical transistorized or integrated circuit control circuits, and it enhances their use in low-power phase control and load-switching applications.

### Features

- Very High Gate Sensitivity
- Low On-State Voltage at High Current Levels
- Glass-Passivated Chip for Stability
- Small, Rugged Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Pb-Free Package is Available\*

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating  | Symbol                                | Value       | Unit             |
|---|---------------------------------------|-------------|------------------|
| Peak Repetitive Off-State Voltage (Note 1) $(T_J = 25 \text{ to } 110^{\circ}\text{C}$ , Gate Open) | V <sub>DRM,</sub><br>V <sub>RRM</sub> | 200         | V                |
| On-State RMS Current (T <sub>C</sub> = 70°C)<br>(Full Cycle Sine Wave 50 to 60 Hz)                  | I <sub>T(RMS)</sub>                   | 2.5         | A                |
| Peak Non–Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_C$ = 70°C)                   | I <sub>TSM</sub>                      | 25          | A                |
| Circuit Fusing Consideration (t = 8.3 ms)   | l <sup>2</sup> t                      | 2.6         | A <sup>2</sup> s |
| Peak Gate Power (Pulse Width $\leq$ 10 $\mu$ s, T <sub>C</sub> = 70°C)                              | P <sub>GM</sub>                       | 10          | W                |
| Average Gate Power (t = 8.3 ms, $T_C = 70^{\circ}C$ )   | P <sub>G(AV)</sub>                    | 0.5         | W                |
| Peak Gate Current<br>(Pulse Width = 10 μs, T <sub>C</sub> = 70°C)                                   | I <sub>GM</sub>                       | 0.5         | A                |
| Operating Junction Temperature Range  | TJ                                    | -40 to +110 | °C               |
| Storage Temperature Range   | T <sub>stg</sub>                      | -40 to +150 | °C               |
| Mounting Torque (6-32 Screw) (Note 2)   | -                                     | 8.0         | in. lb.          |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

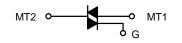
 Torque rating applies with use of torque washer (Shakeproof WD19523 or equivalent). Mounting Torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Main terminal 2 and heat-sink contact pad are common.



# **ON Semiconductor®**

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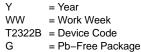
TRIACS 2.5 AMPERES RMS 200 VOLTS





### MARKING DIAGRAM





|   | PIN ASSIGNMENT  |
|---|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate            |

#### **ORDERING INFORMATION**

| Device  | Package              | Shipping      |
|---------|----------------------|---------------|
| T2322B  | TO225AA              | 500 Units/Box |
| T2322BG | TO225AA<br>(Pb–Free) | 500 Units/Box |

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Publication Order Number: T2322/D



# T2322B

## THERMAL CHARACTERISTICS

| Characteristic  | Symbol              | Max | Unit |
|---|---------------------|-----|------|
| Thermal Resistance, Junction-to-Case                                      | $R_{	ext{	heta}JC}$ | 3.5 | °C/W |
| Thermal Resistance, Junction-to-Ambient                                   | $R_{\thetaJA}$      | 60  | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Sec | ΤL                  | 260 | °C   |

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$  unless otherwise noted; Electricals apply in both directions)

| Characteristic   | Symbol          | Min  | Тур      | Max        | Unit     |
|--|-----------------|------|----------|------------|----------|
| OFF CHARACTERISTICS  |                 |      | .76      |            | •        |
| Peak Repetitive Blocking Current<br>$(V_D = Rated V_{DRM}, V_{RRM}; Gate Open)$ $T_J = 25^{\circ}$<br>$T_J = 110^{\circ}$  |                 |      | _<br>0.2 | 10<br>0.75 | μA<br>mA |
| ON CHARACTERISTICS   |                 | •    | •        | •          | •        |
| Peak On-State Voltage (Note 3)<br>$(I_{TM} = \pm 10 \text{ A})$  | V <sub>TM</sub> | -    | 1.7      | 2.2        | V        |
| Gate Trigger Current (Continuous dc)<br>$(V_D = 12 V, R_L = 100 \Omega)$<br>All Quadrants  | I <sub>GT</sub> | -    | -        | 10         | mA       |
| Gate Trigger Voltage (Continuous dc)<br>( $V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_C = 25^{\circ}\text{C}$ )   | V <sub>GT</sub> | -    | 1.0      | 2.2        | V        |
| Gate Non–Trigger Voltage $(V_D = 12 V, R_L = 100 \Omega, T_C = 110^{\circ}C)$  | V <sub>GD</sub> | 0.15 | -        | -          | V        |
| Holding Current<br>( $V_D = 12 V$ , $I_T$ (Initiating Current) = ±200 mA, Gate Open)   | Ι <sub>Η</sub>  | -    | 15       | 30         | mA       |
| Gate Controlled Turn-On Time (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 10 A pk, I <sub>G</sub> = 60 mA, tr = 0.1 $\mu$ sec)                     | t <sub>gt</sub> | -    | 1.8      | 2.5        | μs       |
| DYNAMIC CHARACTERISTICS  | •               | •    |          |            | •        |
| Critical Rate-of-Rise of Off-State Voltage<br>(V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, T <sub>C</sub> = 100°C)                             | dv/dt           | 10   | 100      | -          | V/µs     |
| Critical Rate-of-Rise of Commutation Voltage<br>( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 3.5 A pk, Commutating<br>di/dt = 1.26 A/ms, Gate Unenergized, $T_C$ = 90°C) | dv/dt(c)        | 1.0  | 4.0      | -          | V/µs     |

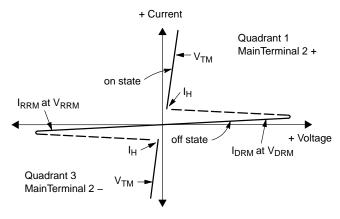
3. Pulse Test: Pulse Width  $\leq$  1.0 ms, Duty Cycle  $\leq$  2%.

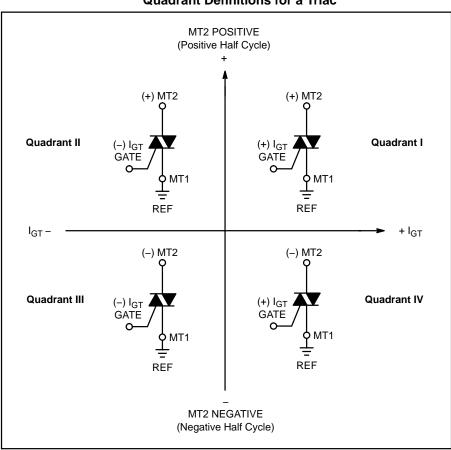


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## Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol           | Parameter                                 |
|------------------|---|
| V <sub>DRM</sub> | Peak Repetitive Forward Off State Voltage |
| I <sub>DRM</sub> | Peak Forward Blocking Current             |
| V <sub>RRM</sub> | Peak Repetitive Reverse Off State Voltage |
| I <sub>RRM</sub> | Peak Reverse Blocking Current             |
| V <sub>TM</sub>  | Maximum On State Voltage                  |
| I <sub>H</sub>   | Holding Current                           |





## **Quadrant Definitions for a Triac**

All polarities are referenced to MT1.

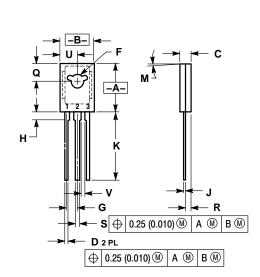
With in-phase signals (using standard AC lines) quadrants I and III are used.



# T2322B

### PACKAGE DIMENSIONS

TO-225 CASE 77-09 **ISSUE Z** 



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI

 Dimensional AID FORCEMENTIAL AND THE ANSI TY 14.5M, 1982.
CONTROLLING DIMENSION: INCH.
077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

|     | INCHES |          |       | IETERS |
|-----|--------|----------|-------|--------|
| DIM | MIN    | MAX      | MIN   | MAX    |
| Α   | 0.425  | 0.435    | 10.80 | 11.04  |
| В   | 0.295  | 0.305    | 7.50  | 7.74   |
| С   | 0.095  | 0.105    | 2.42  | 2.66   |
| D   | 0.020  | 0.026    | 0.51  | 0.66   |
| F   | 0.115  | 0.130    | 2.93  | 3.30   |
| G   | 0.094  | 94 BSC 2 |       | BSC    |
| Н   | 0.050  | 0.095    | 1.27  | 2.41   |
| J   | 0.015  | 0.025    | 0.39  | 0.63   |
| Κ   | 0.575  | 0.655    | 14.61 | 16.63  |
| М   | 5°     | 5° TYP   |       | ТҮР    |
| Q   | 0.148  | 0.158    | 3.76  | 4.01   |
| R   | 0.045  | 0.065    | 1.15  | 1.65   |
| S   | 0.025  | 0.035    | 0.64  | 0.88   |
| U   | 0.145  | 0.155    | 3.69  | 3.93   |
| ٧   | 0.040  |          | 1.02  |        |

MT 1 MT 2 2. 3 GATE

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